

Appl. No. 10/707,703
Amdt. dated June 27, 2006
Reply to Office action of March 31, 2006

REMARKS/ARGUMENTS

This is a full and timely response to the Office action of March 31, 2006. Claim 6 has been amended and new claims 19-20, dependent upon claim 6 have been introduced. Claim changes are supported by Paragraphs [0030]-[0032] and [0034] as filed and Figs.7-10. No new material has been introduced. Reconsideration of claim 6 and consideration of new claims 19-20 is respectfully requested.

The Applicant acknowledges and appreciates the allowance of claims 13-18.

1. Claim Rejections

Claims 6-11 have been rejected under 35 U.S.C. 103(a) as being unpatentable over Goo (5,677,215) in view of Lin et al. (5,933,732).

The applicant has chosen to amend claim 6 to further point out and claim the invention by including the limitations of "a common source" and "a common gate" with the plurality of drain regions. Known prior art utilizes source/drain pairs (for example, Lin et al., Col.9, lines 25-28), rather than a plurality of drain regions sharing a common source and a common gate.

"In contrast to the prior art, the high-density ROM cell according to the present invention has a plurality of drains, a common gate, and a common source. Since such kind of the structure composed of the common devices provides a manner for operating a plurality of drain signals, a single memory cell can store a plurality bits of data, which has a higher density than that of the prior art, and accordingly, the circuit area can be reduced." (Present application, Paragraph [0034]).

For at least these reasons, and because the allowability of dependent claims ultimately depends upon the allowability of their respective base claims, the applicant respectfully requests reconsideration of claims 6-11.

2. Introduction of New Claims

The applicant requests consideration and allowance of new claims 19-20, which depend

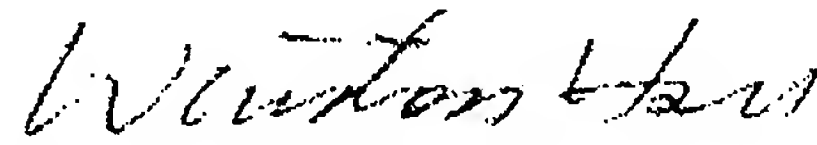
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upon claim 6. Claim 19 introduces limitations of a plurality of bit lines and a switching circuit for selectively accessing data stored in one of the plurality of drain regions (Fig.10). Claim 20 is supported by Paragraph [0031]. No new material has been introduced.

5 Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Sincerely yours,

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